



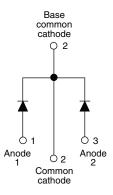
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Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 6 A



TO-247AC



PRODUCT SUMMARY	
Package	TO-247AC
I _{F(AV)}	2 x 6 A
V _R	1200 V
V _F at I _F	2.4 V
t _{rr} typ.	26 ns
T _J max.	150 °C
Diode variation	Single die

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA12PA120C... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. The VS-HFA12PA120C... has basic ratings of 1200 V and 6 A per leg continuous current. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA12PA120C... is ideally suited for applications in power supplies and power conversion systems (such as inverters, converters, UPS systems, and power factor correction circuits), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Cathode to anode voltage	V_{R}		1200	V				
Maximum continuous forward current per leg	_	T 100 °C	6					
per device	l _F	T _C = 100 °C	12	^				
Single pulse forward current	I _{FSM}		80	А				
Maximum repetitive forward current	I _{FRM}		24					
Maximum navvar dissination	D	T _C = 25 °C	62.5	10/				
Maximum power dissipation	P_{D}	T _C = 100 °C	25	W				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C				



VS-HFA12PA120CPbF, VS-HFA12PA120C-N3

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS MIN. TYP.							
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA	1200	-	-					
Maximum forward voltage	V_{FM}	I _F = 6 A	-	2.7	3.0	V				
		I _F = 12 A -		3.5	3.9					
		I _F = 6 A, T _J = 125 °C	-	2.4	2.8					
Maximum reverse		$V_R = V_R$ rated	-	0.26	5.0					
leakage current	I _{RM}	T _J = 125 °C, V _R = 0.8 x V _R rated	-	110	500	μA				
Junction capacitance	C _T	V _R = 200 V	-	9.0	14	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS				
Reverse recovery time	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	26	-				
	t _{rr1}	T _J = 25 °C	I _F = 6 A dI _F /dt = 200 A/μs V _R = 200 V	-	53	80	ns			
	t _{rr2}	T _J = 125 °C		-	87	130				
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.4	8.0	A nC A/μs			
	I _{RRM2}	T _J = 125 °C		-	5.0	9.0				
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	116	320				
	Q _{rr2}	T _J = 125 °C		-	233	585				
Peak rate of fall of recovery current during t _b	dI _{(rec)M} /dt1	T _J = 25 °C		-	180	-				
	dI _{(rec)M} /dt2	T _J = 125 °C		-	100	-				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	2.0					
Thermal resistance, junction to ambient	R _{thJA}	R _{thJA} Typical socket mount		-	80	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.50	-					
Weight			-	2.0	-	g				
vveigni			-	0.07	-	OZ.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC (JEDEC)		HFA12I	PA120C					





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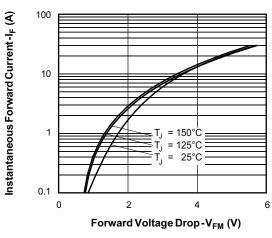


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

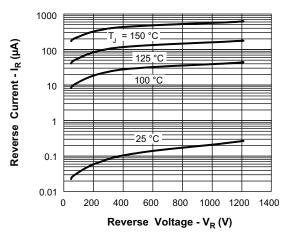


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

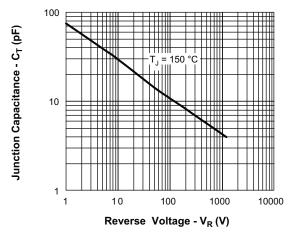


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

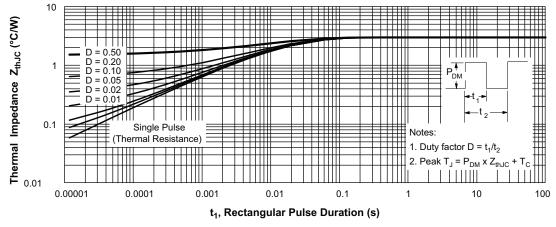


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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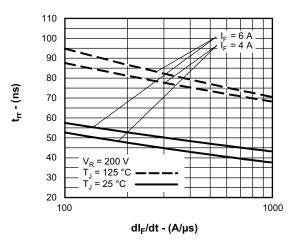


Fig. 5 - Typical Reverse Recovery Time vs. dl_E/dt

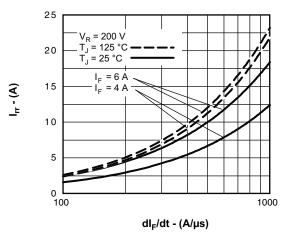


Fig. 6 - Typical Recovery Current vs. dl_F/dt

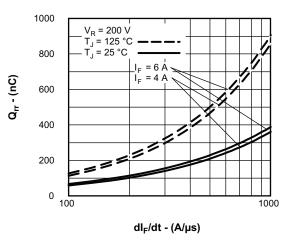


Fig. 7 - Typical Stored Charge vs. dl_F/dt

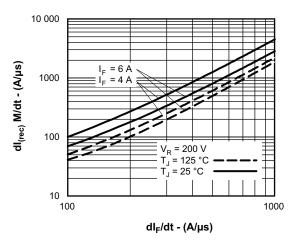


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

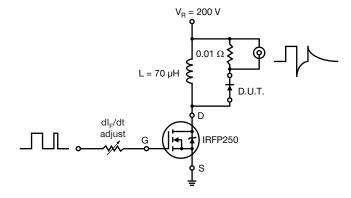
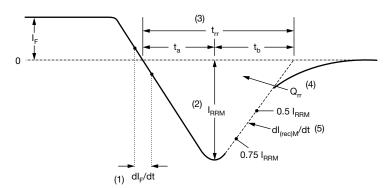


Fig. 9 - Reverse Recovery Parameter Test Circuit

VS-HFA12PA120CPbF, VS-HFA12PA120C-N3

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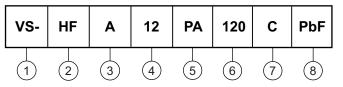


- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}
 - $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (5) dl_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- HEXFRED® family
- 3 Electron irradiated
- Current rating (12 = 12 A)
- **5** PA = TO-247AC
- Voltage rating: (120 = 1200 V)
- Circuit configurationC = common cathode
 - O common camous
- Environmental digit:
 PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-HFA12PA120CPbF	25	500	Antistatic plastic tube							
VS-HFA12PA120C-N3	25	500	Antistatic plastic tube							

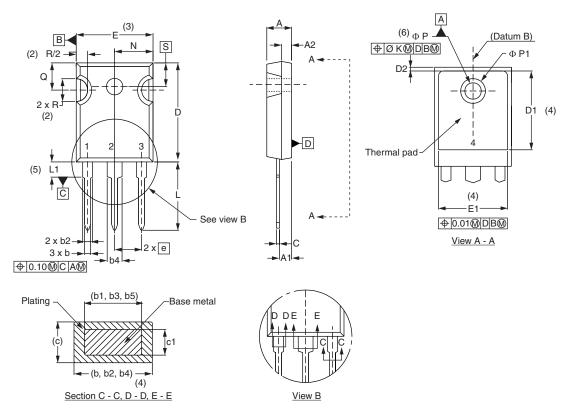
LINKS TO RELATED DOCUMENTS							
Dimensions		www.vishay.com/doc?95542					
Part marking information	TO-247ACPbF	www.vishay.com/doc?95226					
	TO-247AC-N3	www.vishay.com/doc?95007					



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TO-247 - 50 mils L/F

DIMENSIONS in millimeters and inches



CVMPOL	MILLIN	MILLIMETERS		HES	NOTES SY	CVMPOL	MILLIM	IETERS	INC	HES	NOTEC	
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ØK	0.2	254	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			N	7.62 BSC 0.3		.3		
b5	2.59	3.38	0.102	0.133			ØΡ	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	7.39	-	0.291	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	BSC	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



Legal Disclaimer Notice

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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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